Qi Wang

List of Publications by Year in descending order

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62	565	12	23
papers	citations	h-index	g-index
62	62	62	742
all docs	docs citations	times ranked	citing authors

#	Article	IF	CITATIONS
1	Human motion monitoring in sports using wearable graphene-coated fiber sensors. Sensors and Actuators A: Physical, 2018, 274, 132-140.	2.0	7 3
2	Enhanced absorption of graphene strips with a multilayer subwavelength grating structure. Applied Physics Letters, 2014, 105, 221113.	1.5	57
3	Periodic silver nanocluster arrays over large-area silica nanosphere template as highly sensitive SERS substrate. Applied Surface Science, 2018, 437, 92-97.	3.1	47
4	Tracing the Motion of Finger Joints for Gesture Recognition via Sewing RGO-Coated Fibers Onto a Textile Glove. IEEE Sensors Journal, 2019, 19, 9504-9511.	2.4	44
5	Growth of BxGa1â^'xAs, BxAl1â^'xAs and BxGa1â^'xâ^'yInyAs epilayers on (001)GaAs by low pressure metalorganic chemical vapor deposition. Microelectronics Journal, 2009, 40, 87-91.	1.1	30
6	Extremely Low-Threshold Current Density InGaAs/AlGaAs Quantum-Well Lasers on Silicon. Journal of Lightwave Technology, 2015, 33, 3163-3169.	2.7	25
7	RGO-coated elastic fibres as wearable strain sensors for full-scale detection of human motions. Smart Materials and Structures, 2018, 27, 015014.	1.8	25
8	Three-step growth of metamorphic GaAs on Si(001) by low-pressure metal organic chemical vapor deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 051211.	0.6	24
9	Coalescence of GaAs on (001) Si nano-trenches based on three-stage epitaxial lateral overgrowth. Applied Physics Letters, 2015, 106, .	1.5	21
10	LP-MOCVD growth of ternary BxGa1â^'xAs epilayers on (001)GaAs substrates using TEB, TMGa and AsH3. Microelectronics Journal, 2008, 39, 1678-1682.	1.1	18
11	A facile, precise radial artery pulse sensor based on stretchable graphene-coated fiber. Sensors and Actuators A: Physical, 2017, 267, 532-537.	2.0	17
12	First-principle study of the electronic and optical properties of BInGaAs quaternary alloy lattice-matched to GaAs. Physica B: Condensed Matter, 2012, 407, 4570-4573.	1.3	16
13	MOCVD growth and characterizations of BxAl1â^'xAs and BxAl1â^'xâ^'yInyAs alloys. Journal of Alloys and Compounds, 2011, 509, 5631-5636.	2.8	12
14	Highly stretchable and sensitive liquid-type strain sensor based on a porous elastic rope/elastomer matrix composite structure. Composites Science and Technology, 2019, 182, 107707.	3.8	12
15	Multifunctional devices based on SnO ₂ @rGO-coated fibers for human motion monitoring, ethanol detection, and photo response. Nanotechnology, 2018, 29, 195501.	1.3	11
16	MOCVD growth and characterization of multi-stacked InAs/GaAs quantum dots on misoriented Si(100) emitting near 1.3 $\hat{1}$ /4m. Journal of Crystal Growth, 2016, 455, 168-171.	0.7	10
17	Realization of uniaxially strained, rolled-up monolayer CVD graphene on a Si platform via heteroepitaxial InGaAs/GaAs bilayers. RSC Advances, 2017, 7, 14481-14486.	1.7	10
18	Heteroepitaxy of In0.53Ga0.47As on GaAs substrate by low pressure metalorganic chemical vapor deposition for the OEIC applications. Microelectronics Journal, 2006, 37, 700-704.	1.1	9

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19	The saturation density property of (B)InAs/GaAs quantum dots grown by metal-organic chemical vapor deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1146-1151.	1.3	9
20	A flexible and skin-mountable elastic fiber-based sensor patch for healthcare monitoring. Biomedical Physics and Engineering Express, 2019, 5, 045011.	0.6	9
21	The band structures of BSb and B \times Ga1â° \times Sb alloys. Science in China Series G: Physics, Mechanics and Astronomy, 2009, 52, 843-847.	0.2	8
22	Dependence of doubly curved regions on drying method in the fabrication of long-side rolled-up III-V microtubes. Applied Physics Letters, 2013, 103, 051909.	1.5	8
23	Facile fabrication of Au nanoworms covered polyethylene terephthalate (PET) film: Towards flexible SERS substrates. Materials Letters, 2021, 294, 129643.	1.3	8
24	Effect of boron incorporation on the structural and photoluminescence properties of highly-strained lnxGa1-xAs/GaAs multiple quantum wells. AIP Advances, 2013, 3, 072111.	0.6	7
25	Micro-photoluminescence and micro-Raman investigations of rolled-up InGaAs/GaAs microtubes monolithically integrated on silicon. Applied Physics Letters, 2015, 107, 082108.	1.5	7
26	Numerical studies on flow and thermal fields in MOCVD reactor. Science Bulletin, 2010, 55, 560-566.	1.7	6
27	Optically pumped lasing in a rolled-up dot-in-a-well (DWELL) microtube via the support of Au pad. Applied Physics B: Lasers and Optics, 2018, 124, 1.	1.1	5
28	First-principle calculations of dilute nitride GaP1â^'xNx alloy in zinc-blende structures. Physica B: Condensed Matter, 2012, 407, 112-115.	1.3	4
29	The electronic and optical properties of quaternary BxGa1â^'xAs1â^'ySby alloys with low boron concentration: A first-principles study. Journal of Alloys and Compounds, 2013, 563, 18-21.	2.8	4
30	Room temperature observation of optical modes in transferred rolled-up InGaAs/GaAs quantum dot microtube with AlGaAs confining layers. Materials Science in Semiconductor Processing, 2018, 79, 20-23.	1.9	4
31	A robust, flexible adhesive tape-based SERS substrate fabricated by polymer etching and subsequent Au coating on the exposed SiO2 nanosphere monolayer. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2022, 281, 121626.	2.0	4
32	Effects of boron incorporation on the strain and photoluminescence properties of GaAsSb/GaAs quantum wells. Materials Science in Semiconductor Processing, 2013, 16, 1713-1717.	1.9	3
33	Self-rolled-up InGaAs/GaAs microtubes fabricated directly on Si (100) substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 030603.	0.6	3
34	LP-MOCVD growth of BGaAsSb thick layers and BGaAsSb/GaAs quantum well structures on GaAs (001) substrates. Journal of Crystal Growth, 2014, 394, 74-80.	0.7	3
35	Optical studies of free-standing GaAs/AlGaAs single quantum well (SQW) microtubes: A comparison with InGaAs/GaAs bilayer microtubes. Materials Letters, 2016, 166, 263-266.	1.3	3
36	Epitaxial lateral overgrowth of InP/GaAs (100) heterostructures by metalorganic chemical vapor deposition. Microelectronics Journal, 2007, 38, 606-609.	1.1	2

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37	Analysis and simulation of process parameters for epitaxy of InP-based compound semiconductor materials. Proceedings of SPIE, 2008, , .	0.8	1
38	The influence of growth parameters on the formation on InAs/GaAs by MOCVD., 2012, , .		1
39	Selective area growth of InP on lithography-free, nanopatterned GaAs(001) by metalorganic chemical vapor deposition. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 011210.	0.6	1
40	Sensitive Liquid Sensing Using Rolled-Up InAs/GaAs Quantum Dot Microtube Ring Resonator. , 2018, , .		1
41	Experiment on VCSEL Composed of Special Structure DBRs in Integrated Optoelectronic Chip. IEEE Access, 2019, 7, 175622-175627.	2.6	1
42	DWELL based laser structure grown by LP-MOCVD using InGaP as p-doped cladding layer. , 2015, , .		1
43	Facile fabrication of wafer-scale flexible SERS substrate via cryo-transferring SiO2 nanosphere multilayer into waterborne polyurethane (WPU) film. Materials Letters, 2022, 317, 132063.	1.3	1
44	<title>Investigation of InP epitaxial films on GaAs substrate grown by LP-MOCVD</title> ., 2006, 6029, 190.		0
45	Buffer optimization for high-quality InP-on-GaAs(001) quasi-substrates. , 2007, , .		0
46	Growth of B x Ga 1-x As, B x Al 1-x As and B x Ga 1-x-y In y As epilayers on (001)GaAs by LP-MOCVD. Proceedings of SPIE, 2008, , .	0.8	0
47	First-Principles Study of Fundamental Properties of BxIn1-XP Alloys. , 2010, , .		0
48	First-Principles Study of Structural and Electronic Properties of GaNxAs1-X Alloys. , 2010, , .		0
49	The influence of graded In x Ga 1-x As on strain distribution and the band gap in the InAs/GaAs quantum dots. , 2011 , , .		O
50	Effect of boron on the surface and optical properties for (B)InAs/GaAs self-assembled quantum dots grown by MOCVD. , 2011, , .		0
51	First-principles calculations of band-gap properties of zinc-blende B x Ga 1 -x N and B x Ga 1 -x N y As 1 -y alloys. Proceedings of SPIE, 2011 , , .	0.8	0
52	Selective etching of GaAs/Si and InP/GaAs heteroepitaxial wafer. , 2012, , .		0
53	Micro-Raman investigations of free-standing GaAs/AlGaAs single quantum well (SQW) microtubes. , 2015, , .		0
54	Fabrication and performance of In 0.66Ga0.34As0.73P0.27/In 0.89Ga0.11As0.23P0.77 mull tiple-quantum-well lasers. , 2016, , .		0

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55	Graphite oxide-coated Au nanoparticles for improved SERS sensing. , 2016, , .		O
56	Gold nanoparticle-induced diameter reduction and enhanced Raman shift in self-rolled-up InGaAs/GaAs microtubes. , 2016, , .		0
57	1.3 Âμm whispering gallery modes observed in a Si-based rolled-up InAs/GaAs bilayer quantum dot (BQD) microtube at room-temperature. , 2018, , .		O
58	Rolled-up InGaAs/GaAs/RGO trilayer microtubes: Fabrication, characterizations and rolling behaviors. Materials Science in Semiconductor Processing, 2020, 105, 104696.	1.9	0
59	The effect of growth temperature on InAs quantum dots grown by MOCVD. , 2011, , .		O
60	Structural and optical characterization of highly-strained BInGaAs/GaAs quantum wells., 2012,,.		0
61	The LP-MOCVD growth of BGaAs alloys with different gallium precursors. , 2013, , .		0
62	A Wearable Motion Monitoring Fiber Sensor Based on Graphene. , 2017, , .		0